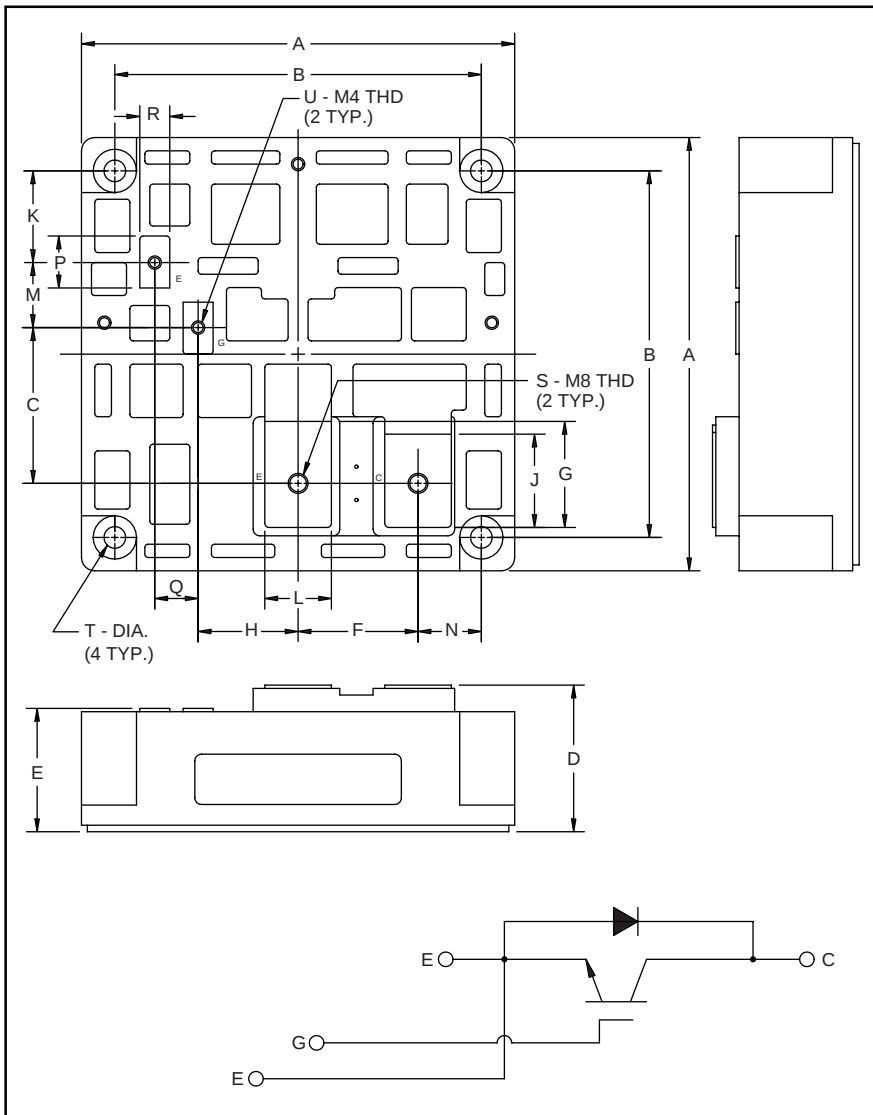


MITSUBISHI IGBT MODULES

CM1000HA-24H

HIGH POWER SWITCHING USE
INSULATED TYPE



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	5.12	130.0
B	4.33±0.01	110.0±0.25
C	1.840	46.75
D	1.73+0.04/-0.02	44.0+1.0/-0.5
E	1.46+0.04/-0.02	37.0+1.0/-0.5
F	1.42	36.0
G	1.25	31.8
H	1.18	30.0
J	1.10	28.0
K	1.08	27.5

Dimensions	Inches	Millimeters
L	0.79	20.0
M	0.77	19.5
N	0.75	19.0
P	0.61	15.6
Q	0.51	13.0
R	0.35	9.0
S	M8 Metric	M8
T	0.26 Dia.	Dia. 6.5
U	M4 Metric	M4



Description:

Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of one IGBT in a single configuration with a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ High Frequency Operation
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies

Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM1000HA-24H is a 1200V (V_{CES}), 1000 Ampere Single IGBT Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	1000	24

CM1000HA-24H**HIGH POWER SWITCHING USE
INSULATED TYPE****Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified**

Ratings	Symbol	CM1000HA-24H	Units
Junction Temperature	T_j	-40 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to +125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	± 20	Volts
Collector Current ($T_C = 25^\circ\text{C}$)	I_C	1000	Amperes
Peak Collector Current ($T_j \leq 150^\circ\text{C}$)	I_{CM}	2000*	Amperes
Emitter Current** ($T_C = 25^\circ\text{C}$)	I_E	1000	Amperes
Peak Emitter Current**	I_{EM}	2000*	Amperes
Maximum Collector Dissipation ($T_C = 25^\circ\text{C}$)	P_C	5800	Watts
Mounting Torque, M8 Main Terminal	—	8.83 ~ 10.8	N · m
Mounting, Torque M6 Mounting	—	1.96 ~ 2.94	N · m
Mounting, Torque M4 Terminal	—	0.98 ~ 1.47	N · m
Weight	—	1600	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{iso}	2500	V_{rma}

*Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(\text{max})}$ rating.

**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{\text{CE}} = V_{\text{CES}}, V_{\text{GE}} = 0\text{V}$	—	—	6	mA
Gate Leakage Current	I_{GES}	$V_{\text{GE}} = V_{\text{GES}}, V_{\text{CE}} = 0\text{V}$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$I_C = 100\text{mA}, V_{\text{CE}} = 10\text{V}$	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	$I_C = 1000\text{A}, V_{\text{GE}} = 15\text{V}$	—	2.7	3.6**	Volts
		$I_C = 1000\text{A}, V_{\text{GE}} = 15\text{V}, T_j = 150^\circ\text{C}$	—	2.4	—	Volts
Total Gate Charge	Q_G	$V_{\text{CC}} = 600\text{V}, I_C = 1000\text{A}, V_{\text{GE}} = 15\text{V}$	—	5000	—	nC
Emitter-Collector Voltage	V_{EC}	$I_E = 1000\text{A}, V_{\text{GE}} = 0\text{V}$	—	—	3.5	Volts

** Pulse width and repetition rate should be such that device junction temperature rise is negligible.

Dynamic Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{ies}	$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = 10\text{V}$	—	—	200	nF
Output Capacitance	C_{oes}		—	—	70	nF
Reverse Transfer Capacitance	C_{res}		—	—	40	nF
Resistive	Turn-on Delay Time	$V_{\text{CC}} = 600\text{V}, I_C = 1000\text{A},$ $V_{\text{GE1}} = V_{\text{GE2}} = 15\text{V}, R_G = 3.3\Omega$	—	—	600	ns
Load	Rise Time		—	—	1500	ns
Switching	Turn-off Delay Time		—	—	1200	ns
Time	Fall Time		—	—	350	ns
Diode Reverse Recovery Time	t_{rr}	$I_E = 1000\text{A}, di_E/dt = -2000\text{A}/\mu\text{s}$	—	—	250	ns
Diode Reverse Recovery Charge	Q_{rr}	$I_E = 1000\text{A}, di_E/dt = -2000\text{A}/\mu\text{s}$	—	7.4	—	μC

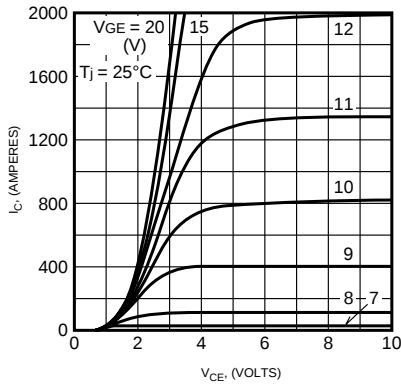
Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)}}$	Per IGBT	—	—	0.022	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)}}$	Per FWDi	—	—	0.050	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{\text{th(c-f)}}$	Per Module, Thermal Grease Applied	—	—	0.018	$^\circ\text{C}/\text{W}$

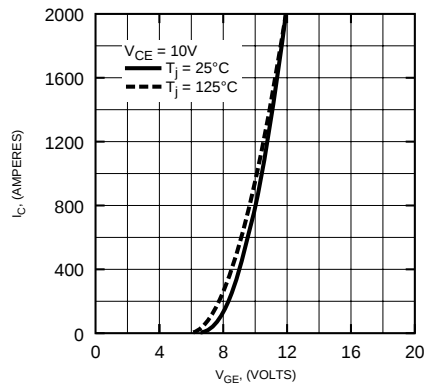
CM1000HA-24H

HIGH POWER SWITCHING USE
INSULATED TYPE

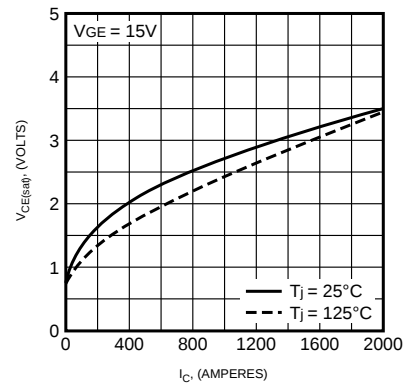
OUTPUT CHARACTERISTICS
(TYPICAL)



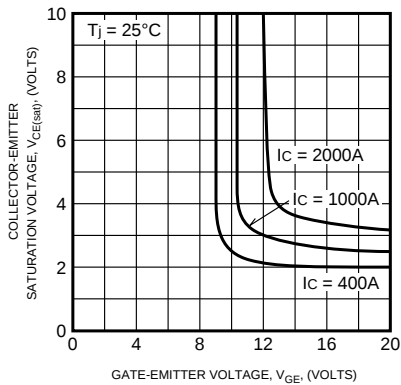
OUTPUT CHARACTERISTICS
(TYPICAL)



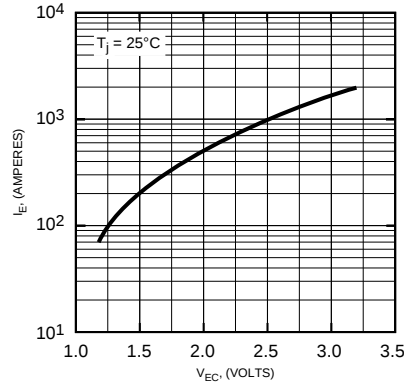
COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



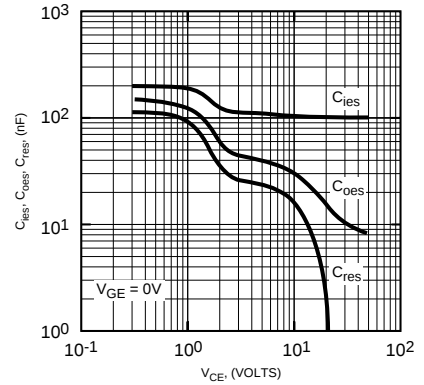
COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



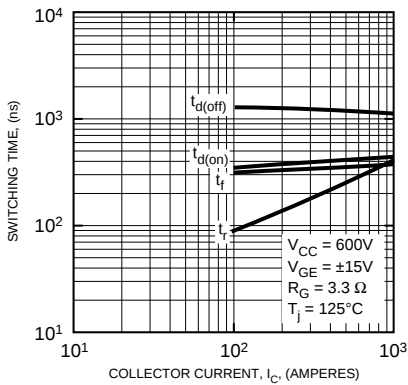
FREE-WHEEL DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



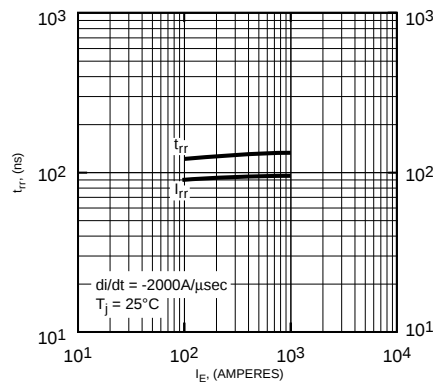
CAPACITANCE VS. V_{CE}
(TYPICAL)



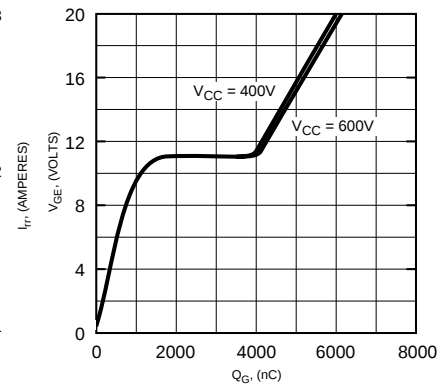
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)



REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)



GATE CHARGE, V_{GE}
(TYPICAL)



CM1000HA-24H

HIGH POWER SWITCHING USE
INSULATED TYPE

